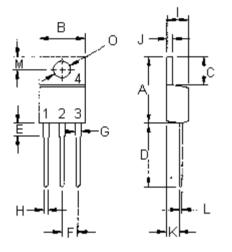




Features:

- Collector-Emitter Sustaining Voltage $V_{CEO (sus)} = 30 \text{ V (Minimum)}$
- Collector-Emitter Saturation Voltage $V_{CE (sat)} = 2 \text{ V (Maximum)}$ at $I_C = 5 \text{ A}$ Reverse-Base SOA 300 V to 400 V at 7 A



Pin 1. Base

- 2. Collector
- 3. Emitter
- 4. Collector (Case)

Dimensions	Minimum	Maximum
Α	14.68	15.31
В	9.78	10.42
С	5.01	8.52
D	13.06	14.62
E	3.57	4.07
F	2.42	3.66
G	1.12	1.36
Н	0.72	0.96
I	4.22	4.98
J	1.14	1.38
K	2.2	2.97
L	0.33	0.55
М	2.48	2.98
0	3.7	3.9

Dimensions: Millimetres

NPN TIP150

7 A Darlington Power Transistors 300 - 400 V 80 W



TO-220

Maximum Ratings

Characteristic	Symbol	TIP150	Unit	
Collector-Emitter Voltage	V _{CEO}	300		
Collector-Base Voltage	V _{CBO}	300	V	
Emitter-Base Voltage	V _{EBO}	8		
Collector Current-Continuous -Peak	I _C	7 10	А	
Base Current	I _B	1.5		
Total Power Dissipation at T _C = 25°C Derate above 25°C	P _D	80 0.64	W W/°C	
Operating and Storage Junction Temperature Range	T _J , T _{STG}	-65 to +150	°C	

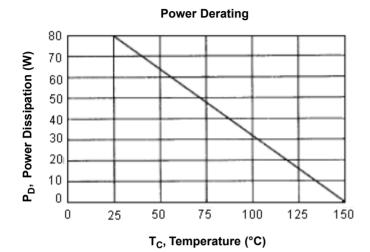
www.element14.com www.farnell.com www.newark.com www.cpc.co.uk





Thermal Characteristics

Characteristic	Symbol	Maximum	Unit
Thermal Resistance Junction to Case	Rθjc	1.56	°C / W



Electrical Characteristics (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Minimum	Maximum	Unit	
Off Characteristics	Off Characteristics				
Collector - Emitter Breakdown Voltage (1) $(I_C = 10 \text{ mA}, I_B = 0)$ TIP150	V _{(BR) CEO}	000	300 -	V	
Collector - Base Breakdown Voltage (1) (I _C = 1 mA, I _B = 0) TIP150	V _{(BR) CBO}	300		V	
Collector Cutoff Current (V _{CE} = 300 V, I _B = 0) TIP150	I _{CEO}	-	250	μА	
Emitter Cutoff Current (V _{EB} = 8 V, I _C = 0)	I _{EBO}	-	15	mA	
On Characteristics (1)					
DC Current Gain $(I_C = 2.5 \text{ A}, V_{CE} = 5 \text{ V})$ $(I_C = 5 \text{ A}, V_{CE} = 5 \text{ V})$ $(I_C = 7 \text{ A}, V_{CE} = 5 \text{ V})$	h _{FE}	150 50 15	-	-	
Collector-Emitter Saturation Voltage ($I_C = 1 \text{ A}, I_B = 10 \text{ mA}$) ($I_C = 2 \text{ A}, I_B = 100 \text{ mA}$) ($I_C = 5 \text{ A}, I_B = 250 \text{ mA}$)	V _{CE} (sat)	-	1.5 1.5 2		
Base-Emitter Saturation Voltage ($I_C = 2 \text{ A}, I_B = 100 \text{ mA}$) ($I_C = 5 \text{ A}, I_B = 250 \text{ mA}$)	V _{BE (sat)}	-	2.2 2.3	V	
Diode Forward Voltage (I _F = 7 A)	V _F	-	3.5		

www.element14.com www.farnell.com www.newark.com www.cpc.co.uk

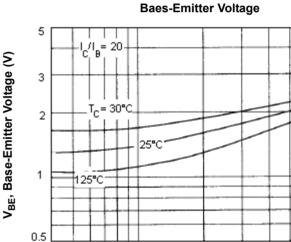




С	haracteristic	Symbol	Minimum	Maximum	Unit
Dynamic Characteristic	:s		1		
Small-Signal Current Ga (I _C = 0.5 A, V _{CE} = 5 V, f		h _{fe}	200	-	-
Output Capacitance (V _{CB} = 10 V, I _E = 0, f = 1	MHz)	C _{ob}	-	150	PF
Switching Characterist	ics		1		
Delay Time	V _{CC} = 250 V, I _C = 5 A	t _d	30 (typical)		200
Rise Time		t _r	180 (typical)		ns
Storage Time	I_{B1} = - I_{B2} = 250 mA tp = 20 μs, Duty Cycle ≤2 %	ts	3.5 (typical)	-	110
Fall Time	.p 20 μ0, Duty Oyolo ±2 //	t _f	1.6 (typical)	1	μs

(1) Pulse Test : Pulse width = 30 µs, duty cycle ≤2%

DC Current Gain 6K T_J = 125°C 2K h_{FE}, DC Current Gain 25°C 1K 500 -30°C 200 100 50 20 10 0.4 2 5 10 0.7 I_C, Collector Current (A)

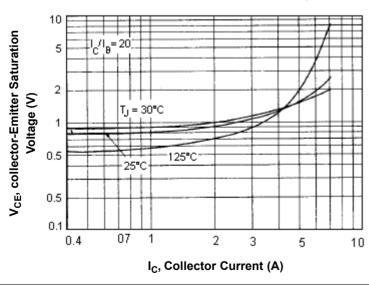


I_C, Collector Current (A)

0.4

0.7

Collector-Emitter Saturation Voltage

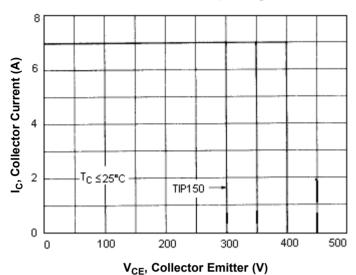


www.element14.com www.farnell.com www.newark.com www.cpc.co.uk

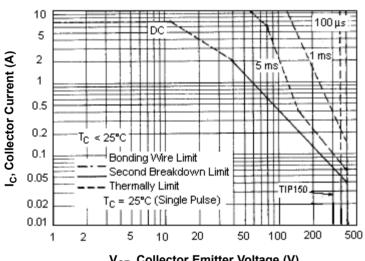




Reverse Biase Safe Operating Area



Active Region Sage Operating Area



V_{CE}, Collector Emitter Voltage (V)

There are two limitations on the power handling ability of a transistor average junction temperature and second breakdown safe operating area curves indicate I_C-V_{CF}: limits of the transistor that must be observed for reliable operation i.e., the transistor must not be subjected to greater dissipation than the curves indicate The data of figure - 6 curve is based on $T_{J(PK)} = 150$ °C; T_{C} is variable depending on power level. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J\,(PK)}$ <150°C. At high case temperatures, thermal limitation will reduce the power that can be handled to values less than the limitations imposed by second breakdown

Part Number Table

Description	Part Number		
Darlington Transistor, TO-220	TIP150		

Important Notice: This data sheet and its contents (the "Information") belong to the members of the Premier Farnell group of companies (the "Group") or are licensed to it. No licence is granted for the use of it other than for information purposes in connection with the products to which it relates. No licence of any intellectual property rights is granted. The Information is subject to change without notice and replaces all data sheets previously supplied. The Information supplied is believed to be accurate but the Group assumes no responsibility for its accuracy or completeness, any error in or omission from it or for any use made of it. Users of this data sheet should check for themselves the Information and the suitability of the products for their purpose and not make any assumptions based on information included or omitted. Liability for loss or damage resulting from any reliance on the Information or use of it (including liability resulting from negligence or where the Group was aware of the possibility of such loss or damage arising) is excluded. This will not operate to limit or restrict the Group's liability for death or personal injury resulting from its negligence. Multicomp is the registered trademark of the Group. © Premier Farnell plc 2012.



